



2.0A Silicon Rectifier

Features

1. High current capability
2. Low reverse leakage current
3. Low forward voltage drop



Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage = Working peak reverse voltage = DC blocking voltage		RL201	V_{RRM}	50	V
		RL202	$=V_{RWM}$	100	V
		RL203	$=V_R$	200	V
		RL204		400	V
		RL205		600	V
		RL206		800	V
		RL207		1000	V
Peak forward surge current			I_{FSM}	60	A
Average forward current	$T_A=75^{\circ}\text{C}$		I_{FAV}	2.0	A
Storage temperature range			T_{stg}	-65~+175	$^{\circ}\text{C}$

Electrical Characteristics

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F=2.0\text{A}$		V_F			1.0	V
Reverse current	$T_A=25^{\circ}\text{C}$		I_R			5.0	μA
	$T_A=100^{\circ}\text{C}$		I_R			50	μA
Diode capacitance	$V_R=4\text{V}, f=1\text{MHz}$		C_D		20		pF

Excel Semiconductor



Characteristics ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

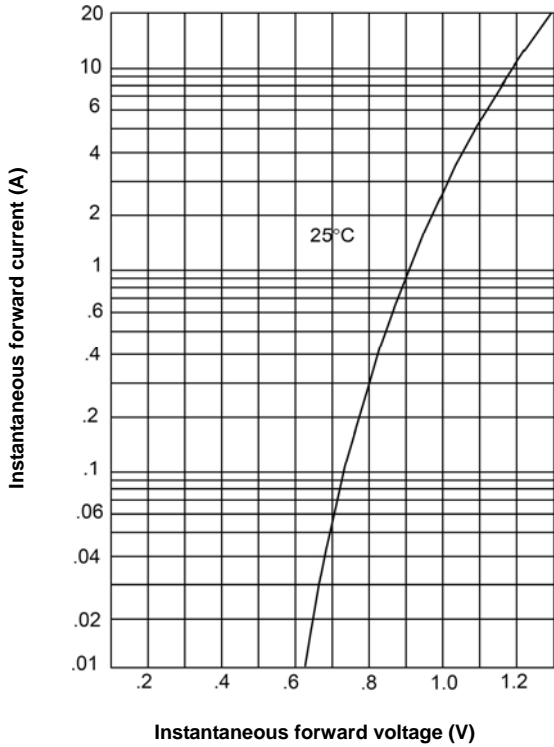


Figure 1. Typical forward characteristics

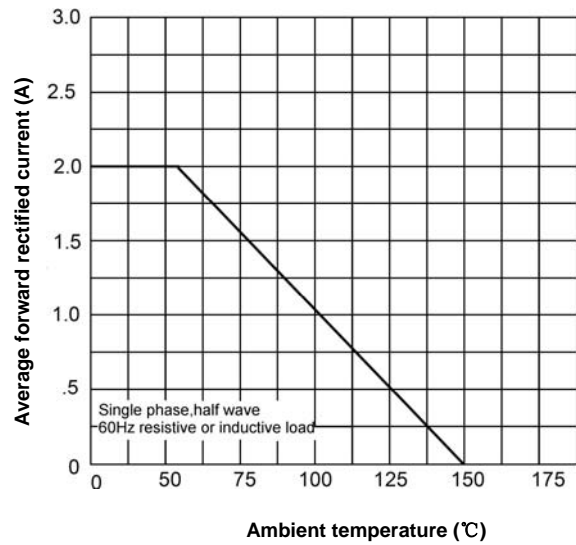


Figure 2. Forward derating curve

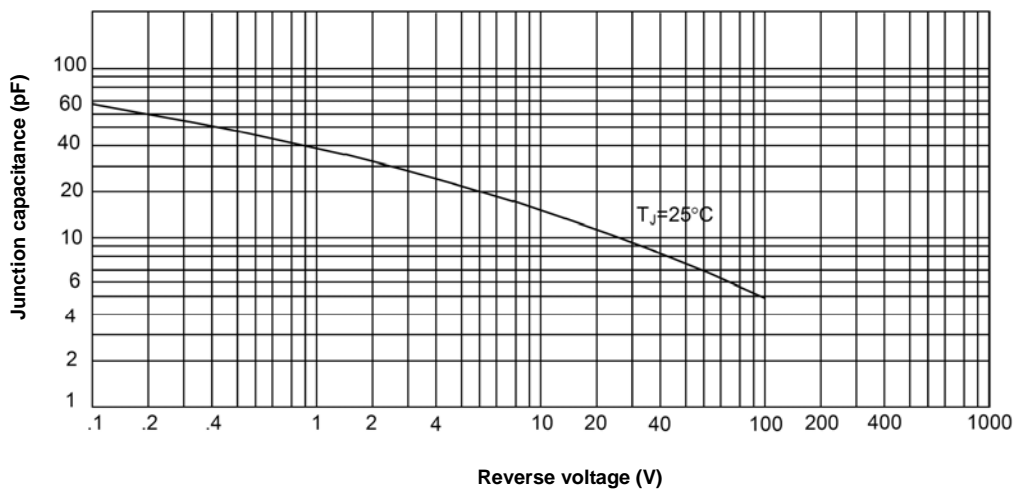
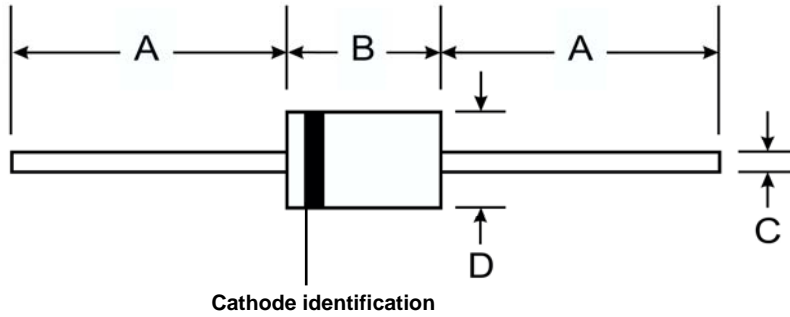


Figure 3. Junction capacitance



Dimensions in mm



DIMENSIONS				
DIM	INCHES		MM	
	MIN	MAX	MIN	MAX
A	1.000	---	25.40	---
B	0.230	0.300	5.80	7.60
C	0.026	0.034	0.70	0.90
D	0.104	0.140	2.60	3.60

Case: molded plastic DO-15

Polarity: cathode band

Marking: type number

Marking

